

ABSTRACT

The invention relates to a method for manufacturing a semiconductor device, and it is an object of the invention to form a semiconductor area formed in island-like patterns as a single crystal or an area which can be regarded as a single crystal, and to 5 simultaneously achieve a laminated structure by which various characteristics of TFTs can be stabilized, wherein an insulation film is formed on a glass substrate, and island-like semiconductor layer is formed thereon. A laser beam passed through a cylindrical lens is made into a linear laser beam and irradiated onto the island-like semiconductor layer by an optical system. The island-like semiconductor layer is subjected to two components, 10 one of which is a direct laser beam component passing through the cylindrical lens and being irradiated directly onto the island-like semiconductor layer, and the other of which is a diffused laser beam component transmitting an insulation film and a substrate, being reflected by a reflection plate, and again transmitting the substrate and insulation film and being irradiated onto the island-like semiconductor layer.